

# MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

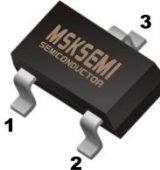

## 2SC1623-MS

Product specification

**FEATURES**

- High DC current gain : $h_{FE}=200$ (Typ)  
 $V_{CE}=6V, I_C=1mA$
- High voltage: $V_{CEO}=50V$

**Reference News**

PACKAGE OUTLINE	MARKING
 <p>1. BASE 2. EMITTER 3. COLLECTOR</p>	
SOT-23	

**MAXIMUM RATINGS (Ta=25°C unless otherwise noted)**

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	60	V
$V_{CEO}$	Collector-Emitter Voltage	50	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current -Continuous	100	mA
$P_C$	Collector Power Dissipation	200	mW
$T_J$	Junction Temperature	150	°C
$T_{stg}$	Storage Temperature	-55-150	°C

**ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)**

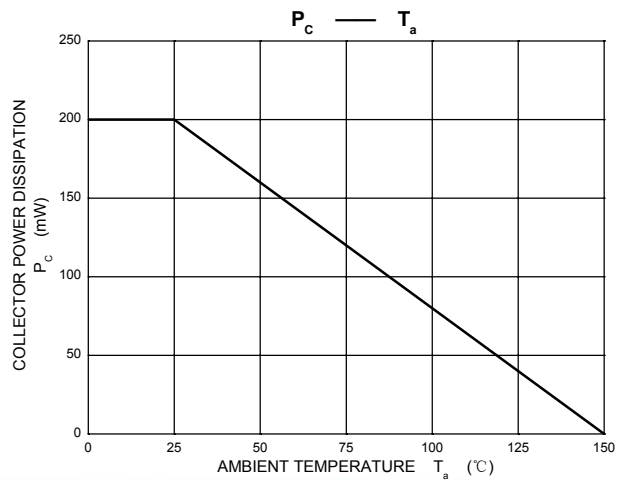
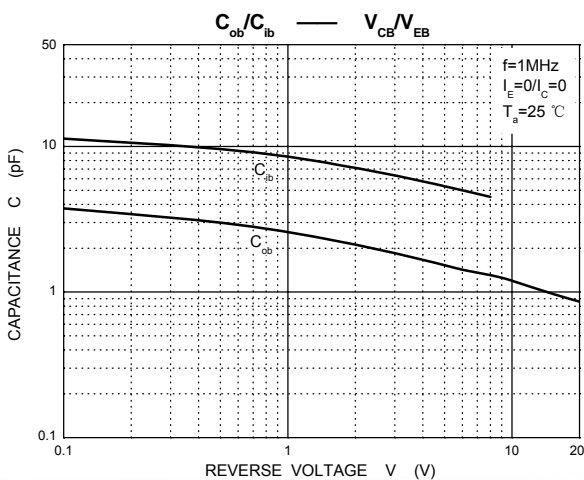
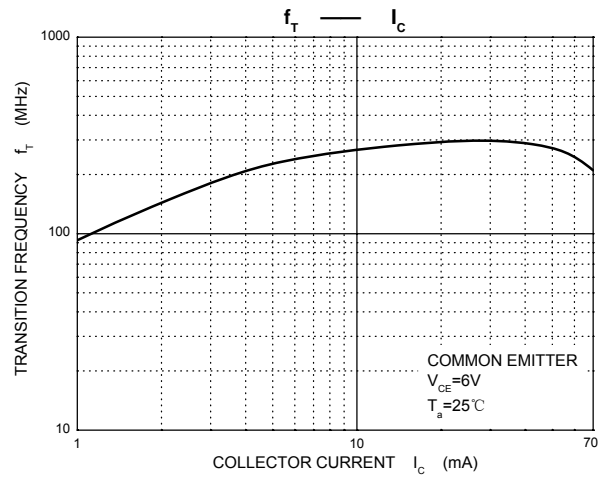
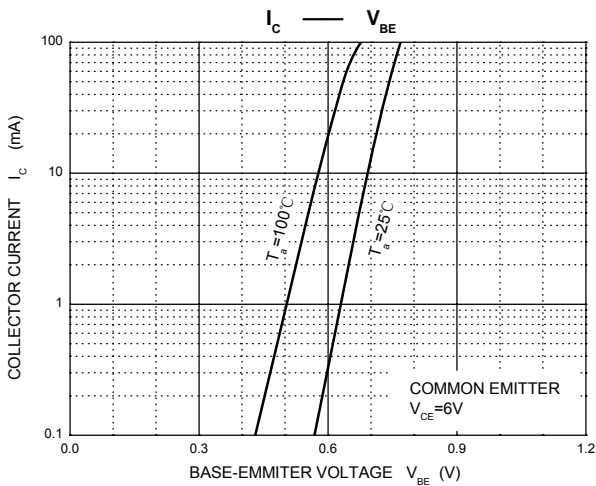
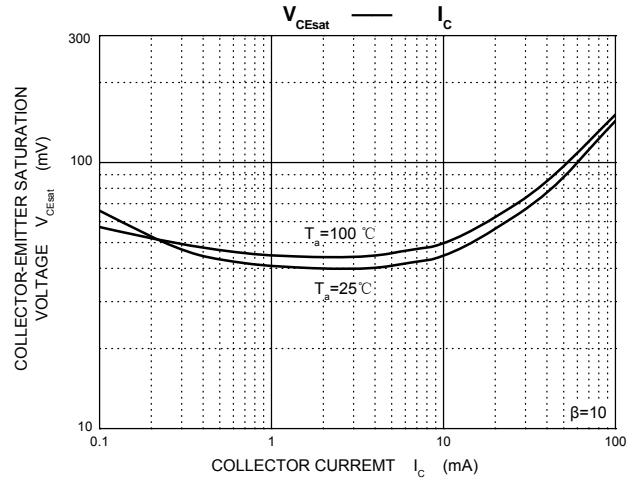
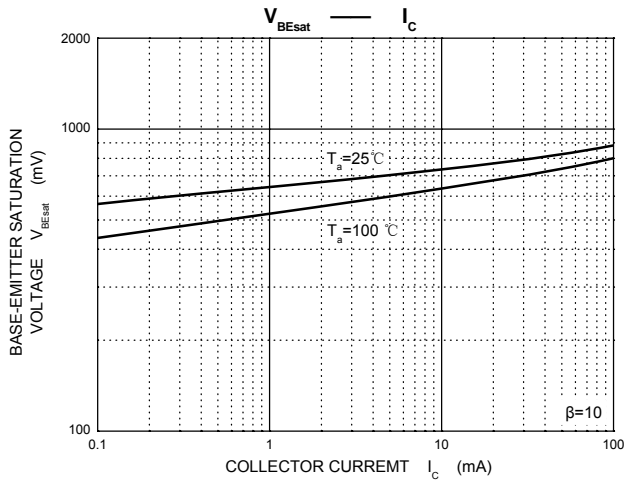
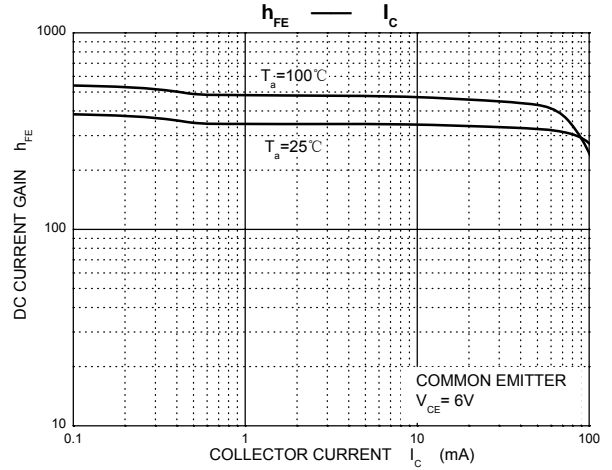
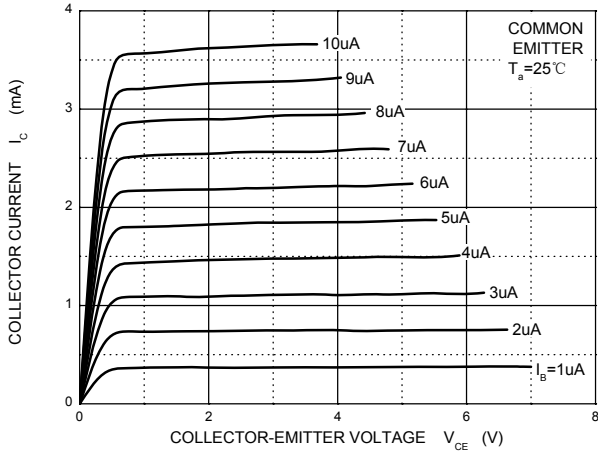
Parameter	Symbol	Test condition.	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=60V, I_E=0$			0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5V, I_C=0$			0.1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE}=6V, I_C=1mA$	90	200	600	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100mA, I_B=10mA$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=100mA, I_B=10mA$			1	V
Transition frequency	$f_T$	$V_{CE}=6V, I_C=10mA$		250		MHz

**CLASSIFICATION OF  $h_{FE}$** 

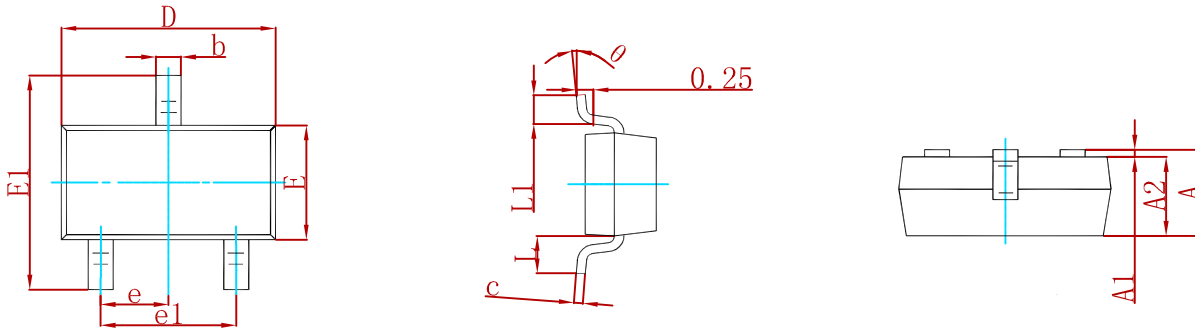
Rank	L4	L5	L6	L7
Range	90-180	135-270	200-400	300-600
Marking	L4	L5	L6	L7

**Typical Characteristics**

**Static Characteristic**

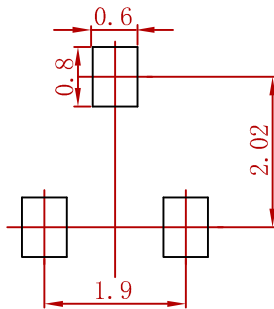


**PACKAGE MECHANICAL DATA**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

**Suggested Pad Layout**



Note:  
 1. Controlling dimension: in millimeters.  
 2. General tolerance: ± 0.05mm.  
 3. The pad layout is for reference purposes only.

**REEL SPECIFICATION**

P/N	PKG	QTY
2SC1623-MS	SOT-23	3000

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